L	Hits	Search Text	B	Time stamp
Number				0.000.000.001
-	319	"electrically isolated electrode"	USPAT;	2002/08/21
			US-PGPUB	08:19
	423	(etch\$3 near3 backside) and conduct\$3 and	USPAT;	2002/08/22
1		insulat\$3	US-PGPUB	09:22
_	5.1	(etch\$3 near3 backside) and conduct\$3 and	USPAT;	2002/08/22
I		insulat\$3 and trench and sidewall	US-PGPUB	10:33
_	101	(etch\$3 near3 backside) and conduct\$3 and	USPAT;	2002/08/26
		insulat\$3 and (trench or channel or	US-PGPUB	14:59
	-	groove or via or hole) and sidewall		
	377	(etch\$3 near3 backside) and conduct\$3 and	USPAT;	12002/08/03
	3,,	insulat\$3 and (trench or channel or	US-PGPUB	10:56
2	t	groove or via or hole)		8
_	107	MEMS and etch\$3 and SOI	USPAT;	2002/08/23
	1 1 1	HEND and econys and sor	US-PGPUB	07:57
	7/3	MEMS and etch\$3 and conduct\$3 and	USPAT;	2002/08/36
	743	insulat\$3 and(trench or groove or via or	US-PGPUB	14:57
		hole or channel)		
j	2700	isolated near3 (electrode or conduct\$3)	USPAT;	2002/08/23
1 -	3709	and etch\$3	US-PGPUB	12:33
	775		USPAT;	2002/08/23
_	//3	insulat\$3 and(trench or cavity or groove	US-PGPUB	14:51
		or via or hole or channel)	05 105 1	
	8	(silicon adj "110") same trench and etch	USPAT;	2002/08/26
_	:	(SIIICON ad) 110 / Same cremen and com	US-PGPUB	09:53
	6220	etch\$3 and conduct\$3 and insulat\$3 and	JPO;	2002/08/26
_	6229	(trench or channel or groove or via or	DERWENT	15:08
		hole or cavity)	22	
		etch\$3 and conduct\$3 and insulat\$3 and	JPO;	2002/08/26
_	1	(trench or channel or groove or via or	DERWENT	15:03
		(trench of channel of groove of via of	DBI WELL	i
T	500	hole or cavity) and MEMS etch\$3 and conduct\$3 and insulat\$3 and	JPO;	200:1/08/37
_	598		DEPWENT	10:43
	1	trench	JPC;	2002/08/27
-	12		DEPWENT	10:44
	1	(microelectromechanical or MEMS)	T DOLLARDIA	